(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
24 September 2026 (24.09.2026)

WIPO | PCT

(10) International Publication Number
WO 2026/198047 A1

(51) International Patent Classification:
H01L 23/522 (2006.01) *H01L 23/498* (2006.01)
H01L 23/528 (2006.01)

(21) International Application Number:
PCT/US2025/020156

(22) International Filing Date:
17 March 2025 (17.03.2025)

(25) Filing Language: English

(26) Publication Language: English

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH,

(54) Title: SILICON NITRIDE LAYER FOR PANEL LEVEL PACKAGING REDISTRIBUTION LAYER

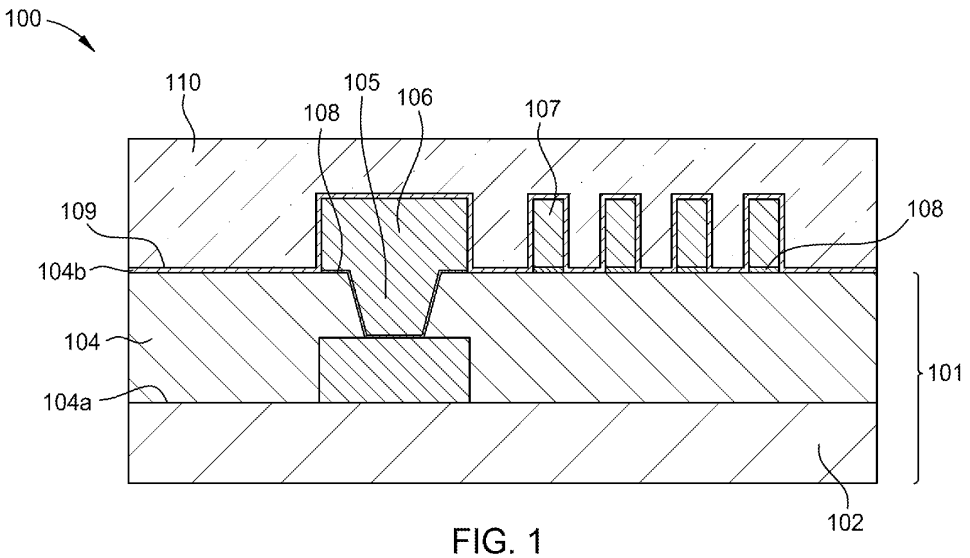


FIG. 1

(57) **Abstract:** Embodiments described herein relate to panel level packaging redistribution layer devices, and methods of making thereof. In one or more embodiments, a device includes a carrier layer. A base layer is disposed over the carrier layer. The base layer has a first surface contacting the carrier layer, and a second surface opposite the first surface. The second surface has a plurality of pillars disposed thereon. A via having an interconnect therein is disposed through the base layer. A silicon and nitrogen containing barrier film is disposed between the insulation layer and each of the base layer, the interconnect, and the plurality of pillars. The silicon and nitrogen containing barrier film has a thickness of about 500 angstroms to about 4000 angstroms. The silicon and nitrogen containing barrier film has a density of about 2 grams per cubic centimeter to about 2.5 grams per cubic centimeter.

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[Continued on next page]

TJ, TM, TN, TR, TT, TZ, UA, UG, US, UY, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) **Designated States** *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

— *of inventorship (Rule 4.17(iv))*

Published:

— *with international search report (Art. 21(3))*